NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.50 \text{ V}$ at $I_F = 5 \text{ A}$

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

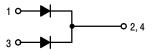


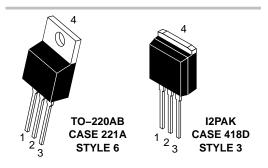
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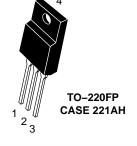
www.onsemi.com

VERY LOW FORWARD VOLT-AGE, LOW LEAKAGE SCHOT-TKY BARRIER RECTIFIERS 30 AMPERES, 120 VOLTS

PIN CONNECTIONS









ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	120	V
Average Rectified Forward Current (Rated V _R , T _C = 125°C)	Per device Per diode	I _{F(AV)}	30 15	A
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz, T _C = 130°C)	Per device Per diode	I _{FRM}	60 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I _{FSM}	150	А
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T _{stg}	-40 to +150	°C
Voltage Rate of Change (Rated V _R)		dv/dt	10,000	V/µs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	NTST30120CTG NTSB30120CT-1G	NTSB30120CTG	NTSJ30120CTG	Unit
Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	2.5 70	1.14 46.6	4.05 105	°C/W

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1)	V _F			V
$(I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.56	_	
$(I_F = 7.5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.71	_	
$(I_F = 15 \text{ A}, T_J = 25^{\circ}\text{C})$		0.90	1.08	
$(I_F = 5 \text{ A}, T_A = 125^{\circ}\text{C})$		0.50	_	
$(I_F = 7.5 \text{ A}, T_J = 125^{\circ}\text{C})$		0.60	_	
(I _F = 15 A, T _J = 125°C)		0.68	0.76	
Maximum Instantaneous Reverse Current (Note 1)	I _R			
$(V_R = 90 \text{ V}, T_J = 25^{\circ}\text{C})$		16	_	μΑ
$(V_R = 90 \text{ V}, T_J = 125^{\circ}\text{C})$		11	_	mA
(Rated dc Voltage, T _J = 25°C)		_	800	μΑ
(Rated dc Voltage, T _J = 125°C)		25	100	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width = $300 \,\mu s$, Duty Cycle $\leq 2.0\%$

NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

TYPICAL CHARACTERISITICS

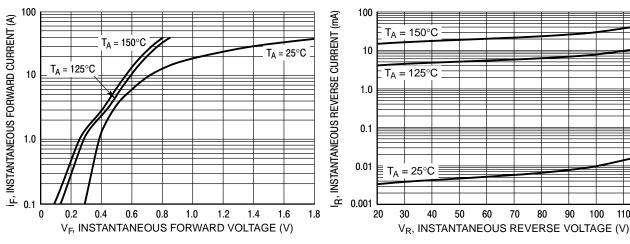


Figure 1. Typical Instantaneous Forward Characteristics

Figure 2. Typical Reverse Current Characteristics

110

120

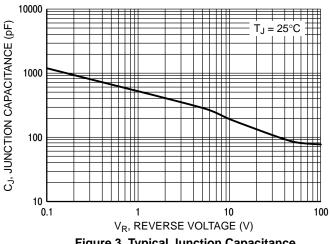


Figure 3. Typical Junction Capacitance

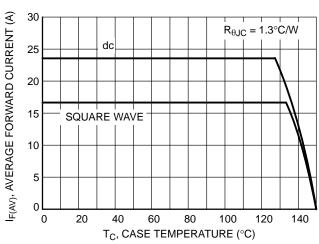
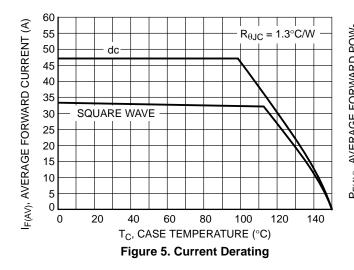


Figure 4. Current Derating per Leg



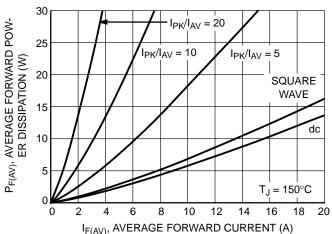


Figure 6. Forward Power Dissipation

NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

TYPICAL CHARACTERISITICS

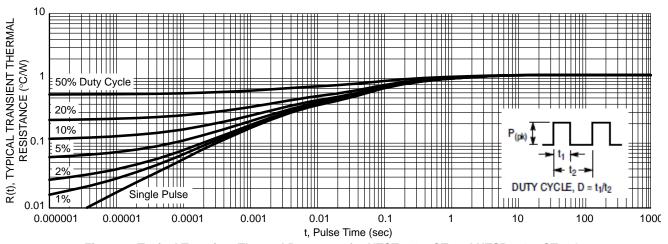


Figure 7. Typical Transient Thermal Response for NTST30120CT and NTSB30120CT-1G

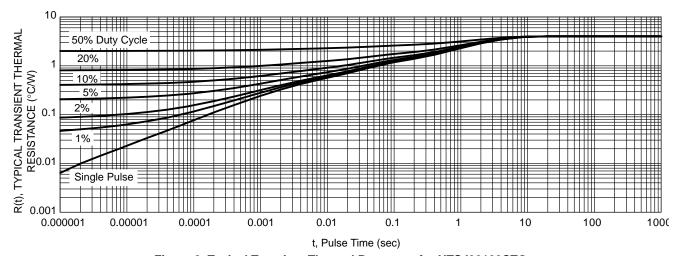


Figure 8. Typical Transient Thermal Response for NTSJ30120CTG

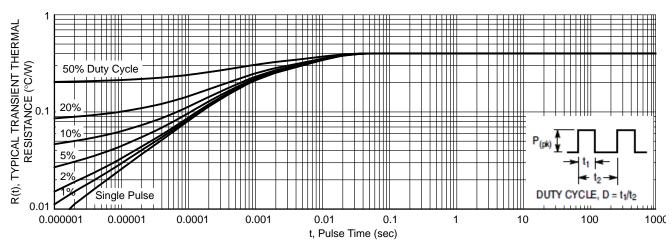


Figure 9. Typical Transient Thermal Response for NTSB30120CTG

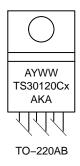
NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

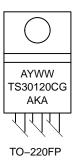
ORDERING INFORMATION

Device	Package	Shipping [†]
NTST30120CTG	TO-220AB (Pb-Free)	50 Units / Rail
NTSJ30120CTG	TO-220FP (Halide-Free)	50 Units / Rail
NTSB30120CT-1G	I ² PAK (Pb-Free)	50 Units / Rail
NTSB30120CTG	D ² PAK (Pb-Free)	50 Units / Rail
NTSB30120CTT4G	D ² PAK (Pb-Free)	800 / Tape & Reel

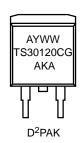
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MARKING DIAGRAMS









A = Assembly Location

Y = Year

WW = Work Week
AKA = Polarity Designator

x = G or H

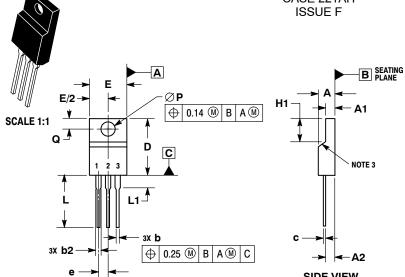
G = Pb-Free Package

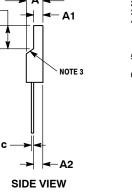
H = Halide-Free Package



ISSUE F

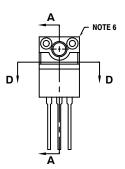
DATE 30 SEP 2014

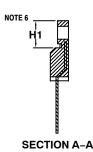






FRONT VIEW





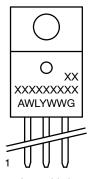
ALTERNATE CONSTRUCTION

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR UNCONTROLLED IN THIS AREA.
- CONTOUR ONCOUNT HOLLED IN THIS AREA.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
 DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION.
 LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
- CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS AT AND H1 FOR MANUFACTURING PURPOSES.

	THE THE CONTRACTOR			
	MILLIMETERS			
DIM	MIN	MAX		
Α	4.30	4.70		
A1	2.50	2.90		
A2	2.50	2.90		
b	0.54	0.84		
b2	1.10	1.40		
С	0.49	0.79		
D	14.70	15.30		
E	9.70	10.30		
е	2.54	BSC		
H1	6.60	7.10		
L	12.50	14.73		
L1		2.80		
P	3.00	3.40		
Q	2.80	3.20		

GENERIC MARKING DIAGRAM*



= Assembly Location

WL = Wafer Lot

= Year

WW = Work Week

G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:		STYLE 2:	
PIN 1.	MAIN TERMINAL 1	PIN 1.	CATHODE
2.	MAIN TERMINAL 2	2.	ANODE
3.	GATE	3.	GATE

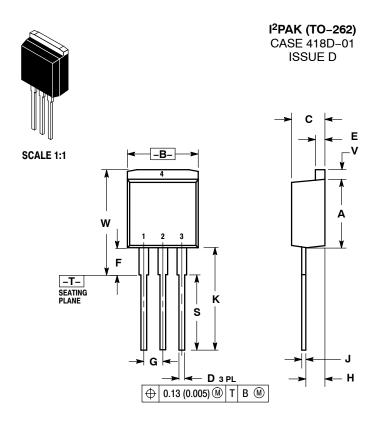
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DESCRIPTION:	TO-220 FULLPACK, 3-LEA	AD	PAGE 1 OF 1

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®





DATE 16 OCT 2007

NOTES:

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- 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.335	0.380	8.51	9.65
В	0.380	0.406	9.65	10.31
С	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
Е	0.045	0.055	1.14	1.40
F	0.122	REF	3.10 REF	
G	0.100	BSC	2.54	BSC
Н	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
K	0.500	0.562	12.70	14.27
S	0.390	0.390 REF		REF
٧	0.045	0.070	1.14	1.78
W	0.522	0.551	13.25	14.00

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:
PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. GATE
2. COLLECTOR	2. DRAIN	2. CATHODE	2. COLLECTOR
EMITTER	SOURCE	3. ANODE	3. EMITTER
COLLECTOR	4. DRAIN	4. CATHODE	 COLLECTOR

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MECHANICAL CASE OUTLINE

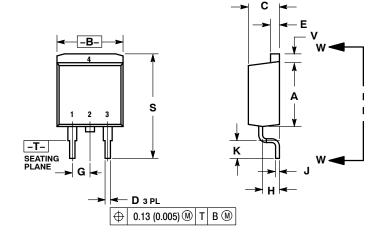




D²PAK 3 CASE 418B-04 **ISSUE L**

DATE 17 FEB 2015

SCALE 1:1



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
Е	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
Н	0.080	0.110	2.03	2.79
7	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
Р	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
٧	0.045	0.055	1.14	1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6: PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE

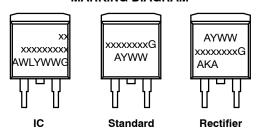
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DATE 17 FEB 2015

GENERIC MARKING DIAGRAM*



xx = Specific Device Code A = Assembly Location

 WL
 = Wafer Lot

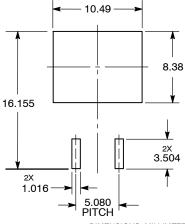
 Y
 = Year

 WW
 = Work Week

 G
 = Pb-Free Package

 AKA
 = Polarity Indicator

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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